





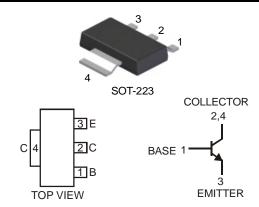
LOW V_{CE(SAT)} NPN SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Low Collector-Emitter Saturation Resistance $R_{CE(SAT)} = 80 \text{m}\Omega$ at 3A
- High DC Current Gain h_{FE} > 400 at I_C = 2A
- Complementary PNP Type Available (DPLS325E)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
 Ordering Information: See Page 3
 Weight: 0.112 grams (approximate)



Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	20	V
Collector-Emitter Voltage	V _{CEO}	20	V
Emitter-Base Voltage	V _{EBO}	5	V
Continuous Collector Current	Ic	3	A
Peak Pulse Current	I _{CM}	8	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation @T _A = 25°C (Note 3)	P _D	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @T _A = 25°C	$R_{ hetaJA}$	125	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Device mounted on FR-4 PCB, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Off Characteristics					ā.	
Collector-Base Breakdown Voltage	V _{(BR)CBO}	20	_	_	V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	20		_	V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	_	_	V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_	_	100	nA	$V_{CB} = 16V, I_{E} = 0$
Emitter Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 4V, I_{C} = 0$
On Characteristics (Note 4)						
		_	0.04	0.10		$I_C = 0.1A$, $I_B = 0.5mA$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.18	0.50	V	$I_C = 2A$, $I_B = 10mA$
		_	0.24	0.45		$I_C = 3A$, $I_B = 20mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	_	0.9	V	$I_C = 1A$, $I_B = 10mA$
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_	_	0.9	V	$V_{CE} = 2V$, $I_C = 1A$
		500	_	_		$V_{CE} = 2V, I_{C} = 0.1A$
DC Current Gain	h _{FE}	400	_	_	_	$V_{CE} = 2V, I_{C} = 2A$
		150		_		$V_{CE} = 2V$, $I_C = 6A$
AC Characteristics						
Transition Frequency	f _T	150		_	MHz	$V_{CE} = 5V, I_{C} = 50mA, f = 50MHz$
Input Capacitance	C _{ibo}	_	230	_	pF	$V_{EB} = 0.5V, f = 1MHz$
Output Capacitance	C _{obo}		23		pF	V _{CB} = 10V, f = 1MHz
Switching Times	t _{on}	_	26	_	ns	$V_{CC} = 10V, I_C = 500mA$
Owntoning riffes	t _{off}	_	220		ns	$I_{B1} = -I_{B2} = 50 \text{mA}$

4. Pulse Test: Pulse width ≤300μs. Duty cycle ≤2.0%.

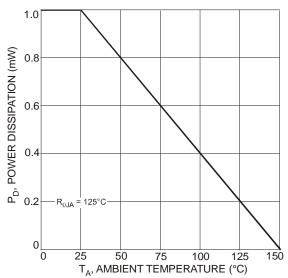


Fig. 1 Max Power Dissipation vs. Ambient Temperature

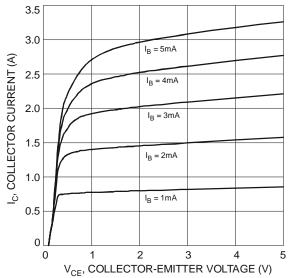


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage



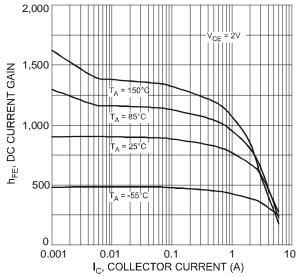
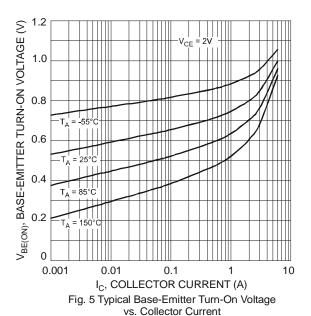


Fig. 3 Typical DC Current Gain vs. Collector Current



0.5

| Collector Characteristics | Collector | Collector Characteristics | Collector Characteristics | Collector |

I_C, COLLECTOR CURRENT (A)
Fig. 4 Typical Collector-Emitter Saturation Voltage
vs. Collector Current

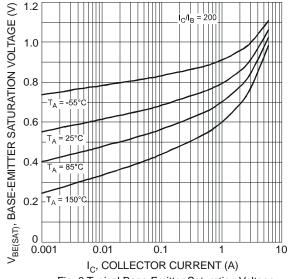


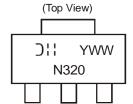
Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping	
DNLS320E-13	SOT-223	2500/Tape & Reel	

Notes: 5. For packaging details, go to our website at http://www.diodes.com/ap2007.pdf.

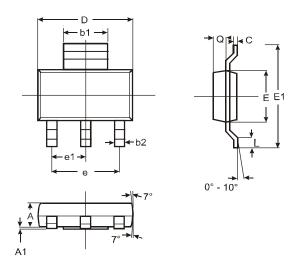
Marking Information



N320 = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

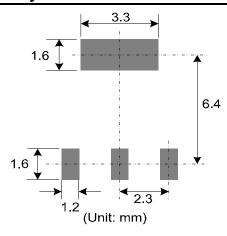


Package Outline Dimensions



	SOT-223					
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b1	2.90	3.10	3.00			
b2	0.60	0.80	0.70			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
Е	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	_	_	4.60			
e1			2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All Dimensions in mm						

Suggested Pad Layout:



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